

# **Power Gallium Nitride (GaN) FETs** Efficient and effective power FETs

Whether for low- or high-power conversion applications, power Gallium Nitride FETs (GaN FETs) are increasingly making their way into mainstream markets. For a variety of 650 V and 150 V applications GaN FETs deliver the fastest transition/switching capability (highest dv/dt and di/dt), and best power efficiency. Additionally, Nexperia power GaN FETs bring enhanced power density through reduced conduction and switching losses. Nexperia GaN FETs are available in 2 configurations:

## Enhancement mode (e-mode)

### (for ≤ 150 V high-power & 650 V low-power applications)

- > Enhancement mode transistor-normally off power switch
- > Ultra-high switching frequency
- > Leading soft-switching performance
- > No reverse-recovery charge
- > Low gate charge, low output charge
- > High performance (>99% efficiency)
- > Tight dynamic characteristics
- > Easy to drive, 0 to 5 V gate drive
- Qualified for industrial applications according to JEDEC standard

#### Key applications ≤ 150 V high-power

- > 400 V-48 V LLC converter for datacenters
- > 48 V to POL direct conversion
- > Power supply (AC/DC) fast-charging for e-mobility
- > USB-C power delivery fast-charging for portables
- > LiDAR (non-automotive)
- > Class D audio amplifiers

#### Key applications 650 V low-power

- > Datacom and telecom (AC/DC and DC/DC)
- > Photovoltaic (PV) micro inverter (DC/AC)
- > Industrial (DC/AC)
- > BLDC / micro servo motor drives
- > LED driver
- > TV power supply unit (PSU)

#### Cascode mode

#### (for 650 V high-power applications)

- > 3 times lower inductances than industry-standard packages for lowest switching losses & EMI
- > Higher reliability compared to wire-bonded solutions
- > 99% power conversion efficiency
- > Up to 1 MHz in soft-switching (high power density)
- > Easy to design gate drive, 0 to 12 V
- > Low R<sub>th(i-mb)</sub> typ for optimal cooling & 175 °C rated
- > Virtually no Q<sub>rr</sub>
- Flexible gull winged leads for temperature cycling & board level reliability
- > MSL1 & Halogen free qualifications

#### Key applications 650 V high-power Industry 4.0

- > Servo motor drives/ frequency inverters
- > Telecom power supplies
- > Class-D Audio amplifiers
- > Welding machines

#### The path to Net Zero CO,

- > Solar (PV) inverters
- > Server Titanium grade power supplies
- > Battery storage/ UPS inverters
- > Heat pumps



nexperia

EFFICIENCY WINS.

#### Power GaN FETs product portfolio

#### Industrial 650 V SMD and through-hole GaN FETs

Package	Type name	Configuration	V <sub>DS</sub> [max] (V)	R <sub>DS(on)</sub> [max] @ V <sub>GS</sub> = 6 V or 10 V (mΩ)	I <sub>D</sub> (max) (A)	Q <sub>c</sub> (nC)	Q <sub>oss</sub> (nC)
CCPAK1212 (SMD)	GAN039-650NBB	Cascode	650	39	59		150
CCPAK1212i (SMD)	GAN039-650NTB			39	60		150
TO-247 (Through-hole)	GAN063-650WSA			60	35		125
	GAN041-650WSB			41	47		150
	GAN111-650WSB			111			
DFN8080 (SMD)	GAN080-650EBE	E-mode		80	29	6.2	60
	GAN140-650FBE			140	17	3.5	33
	GAN190-650FBE			190	11.5	2.8	24.5
DFN5060 (SMD)	GAN140-650EBE			140	17	3.5	33
	GAN190-650EBE			190	11.5	2.8	25

#### Industrial 100 - 150 V WLCSP & LGA GaN FETs

Package	Type name	Configuration	V <sub>ps</sub> [max] (V)	R <sub>DS(on)</sub> [max] @ V <sub>GS</sub> = 5 V (mΩ)	I <sub>p</sub> (max) (A)	Q <sub>c</sub> (nC)	Q <sub>oss</sub> (nC)
WLCSP8 (SMD)	GAN3R2-100CBE	E-mode	100	3.2	60	9.2	50
FCLGA3 (SMD)	GAN7R0-150LBE		150	7	28	7.6	46.8

#### The innovators of copper-clip package technology

Nexperia brings 20 years' experience of producing high-quality, highly robust, copper-clip SMD packaging to the power GaN FET portfolio.

For added flexibility in designs and to further improve heat dissipation, CCPAK is available in both top-side cooling (CCPAK1212) and bottom-side cooling package designs (CCPAK1212i).







For more information on Nexperia GaN FETs, including datasheets, application notes, videos, blogs, news and more. Visit nexperia.com/gan-fets

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